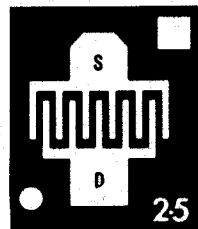


CHIP NUMBER

**FN2.5**



.013"  
(0.737mm)

.012"  
(0.305mm)

Die Size: 12 x 13 (mils)  
0.305 x .0330(mm)  
3 x 3 (mils)  
Pad Size: 0.076 x 0.076(mm)  
GATE-SUBSTRATE

### CONTACT METALLIZATION

Top Contact: > 12,000  
Å Aluminum

Backside Contact: 3,000 Å Gold

### ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the die be eutectically mounted with gold silicon preform 98/2%.
- 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

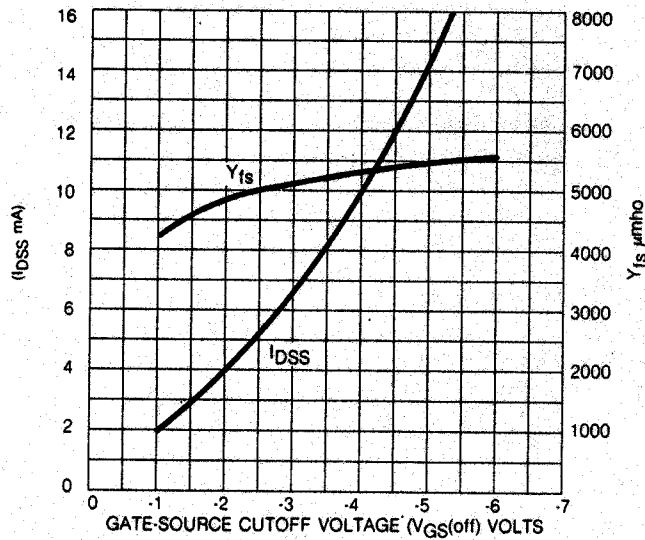
## TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	-25	-35	-50	V	$V_{DS} = 0V, I_G = 1\mu A$
$I_{DSS}$	1.0	10	30	mA	$V_{DS} = 15V, V_{GS} = 0$
$g_{fs}$	3.0	5.5	7.5	mmho	$V_{DS} = 15V, V_{GS} = 0$
$I_{GSS}$		-5.0	-100	pA	$V_{GS} = -20V, V_{DS} = 0$
$r_{DS}$	100	170	500	$\Omega$	$V_{DS} = 100mV, V_{GS} = 0$
$V_{GS(off)}$	-0.8	-3.0	8.0	V	$V_{DS} = 15V, I_D = 1nA$
$C_{rss}$	0.6	0.7	0.9	pF	$V_{DS} = 15V, V_{GS} = 0, f = 1MHz$
$C_{iss}$	3.0	3.5	4.0	pF	$V_{DS} = 15V, V_{GS} = 0, f = 1MHz$
$\bar{e}_n$		15		nV/ $\sqrt{Hz}$	$V_{DG} = 15V, I_D = 5\mu A, f = 100Hz$

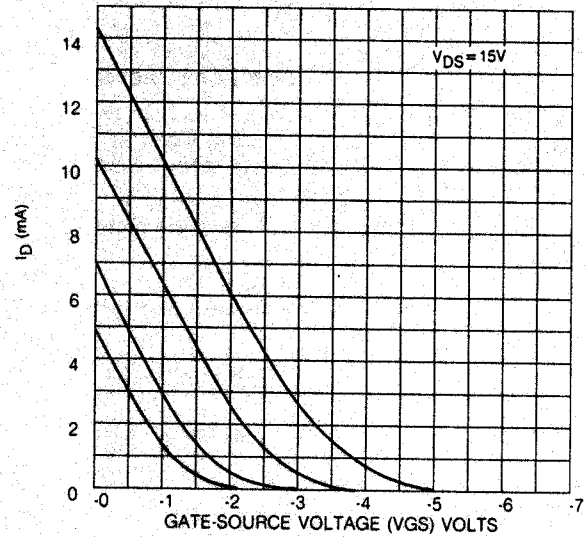
TYPICAL DEVICE TYPES: 2N4116, 2N3823, 2N3452, 2N5104, 2N5105, UC734, 2N5485

CHIP TYPE FN2.5

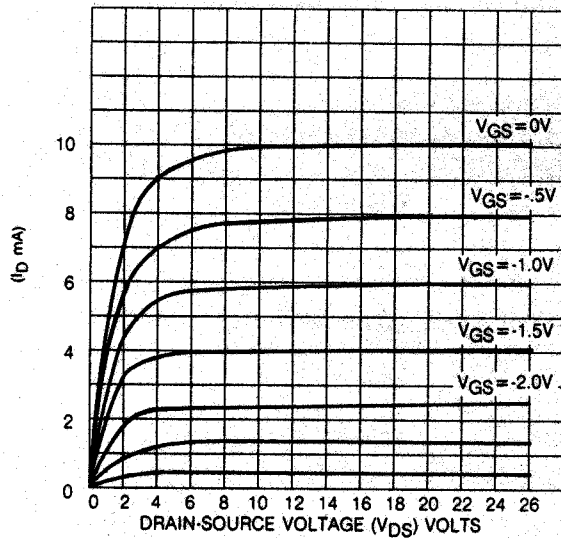
TRANSFER ADMITTANCE VS  
GATE-SOURCE CUTOFF VOLTAGE



TRANSFER CHARACTERISTICS



OUTPUT CHARACTERISTICS



NORMALIZED FORWARD TRANSFER ADMITTANCE  
VS TEMPERATURE

